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Highly Selective FET-type Glucose Sensor based on Shape-controlled Palladium Nanoflower-decorated Graphene.

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Graphical abstract

The high selective FET-type glucose sensor based on GOx/Nafion/SPNFG is fabricated. The high selective FET-type glucose sensor based on GOx/Nafion/SPNFG is fabricated. The detection limit is a 1 nM and sensitivity is increases with sharpening the shape of palladium. Also high selectivity is achieved by nafion layer and glucose

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